ESD5V5U5ULC

Ultra-low capacitance ESD / transient / surge protection array

TVS (transient voltage suppressor)
5.5 V, 0.45 pF, RoHS compliant

Feature list

- ESD/transient protection of high speed data lines exceeding:
  - IEC61000-4-2 (ESD): ±25 kV (air/contact)
  - IEC61000-4-4 (EFT): ±2.5 kV/±50 A (5/50 ns)
  - IEC61000-4-5 (Surge): ±6 A (8/20 µs)
- Maximum working voltage: V_{RWM} = 5.5 V
- Extremely low capacitance: C_L = 0.45 pF I/O to GND (typical)
- Very low dynamic resistance: R_{DYN} = 0.2 Ω (typical) I/O to GND
- Very low reverse clamping voltage: V_{CL} = 9 V (typical) at I_{PP} = 16 A
- Protection of V_{BUS} with one line freely selectable

Potential applications

- Protection of all I/O and V_{BUS} lines in dual USB2.0 ports
- 10/100/1000 Ethernet
- DVI, HDMI, FireWire

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Device information

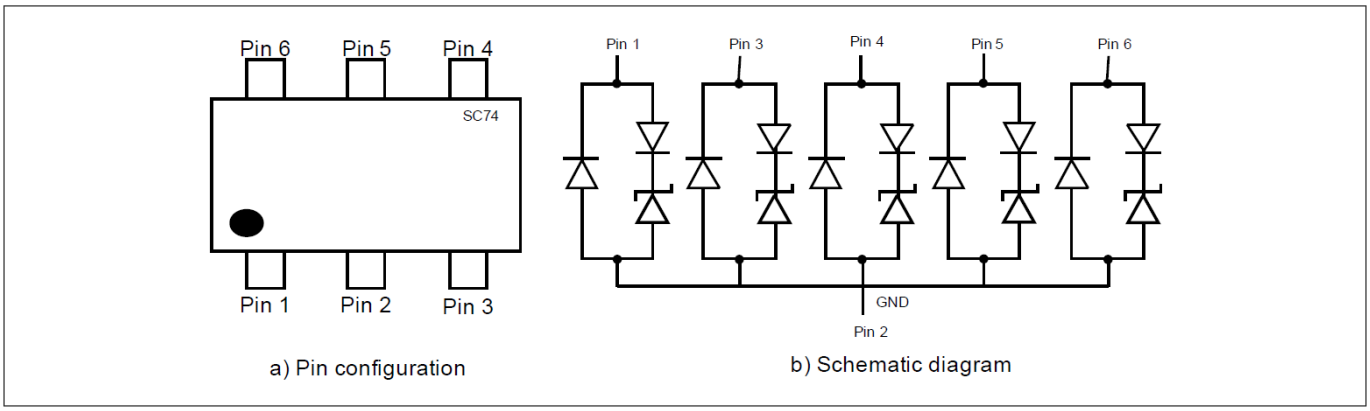

Figure 1 Pin configuration and schematic diagram

Table 1 Part information

Type	Package	Configuration	Marking code
ESD5V5U5ULC	PG-SC74-6-2	5 lines, uni-directional	20

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1 Maximum ratings

Note: *T_A = 25 °C, unless otherwise specified.*

Table 2 Maximum ratings

Parameter	Symbol	Values	Unit	Note or test condition
ESD contact discharge [1)]	V_{ESD}	±25	kV	–
Peak pulse current [2)]	I_{PP}	±6	A	t_p = 8/20 µs
Operating temperature range	T_{OP}	-40 to 125	°C	–
Storage temperature	T_{stg}	-65 to 150	°C	–

Attention: ***Stresses above the maximum values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings. Exceeding only one of these values may cause irreversible damage to the component.***

1 V_{ESD} according to IEC61000-4-2
2 I_{PP} according to IEC61000-4-5

2 Electrical characteristics

Note: *T_A = 25 °C, unless otherwise specified.*

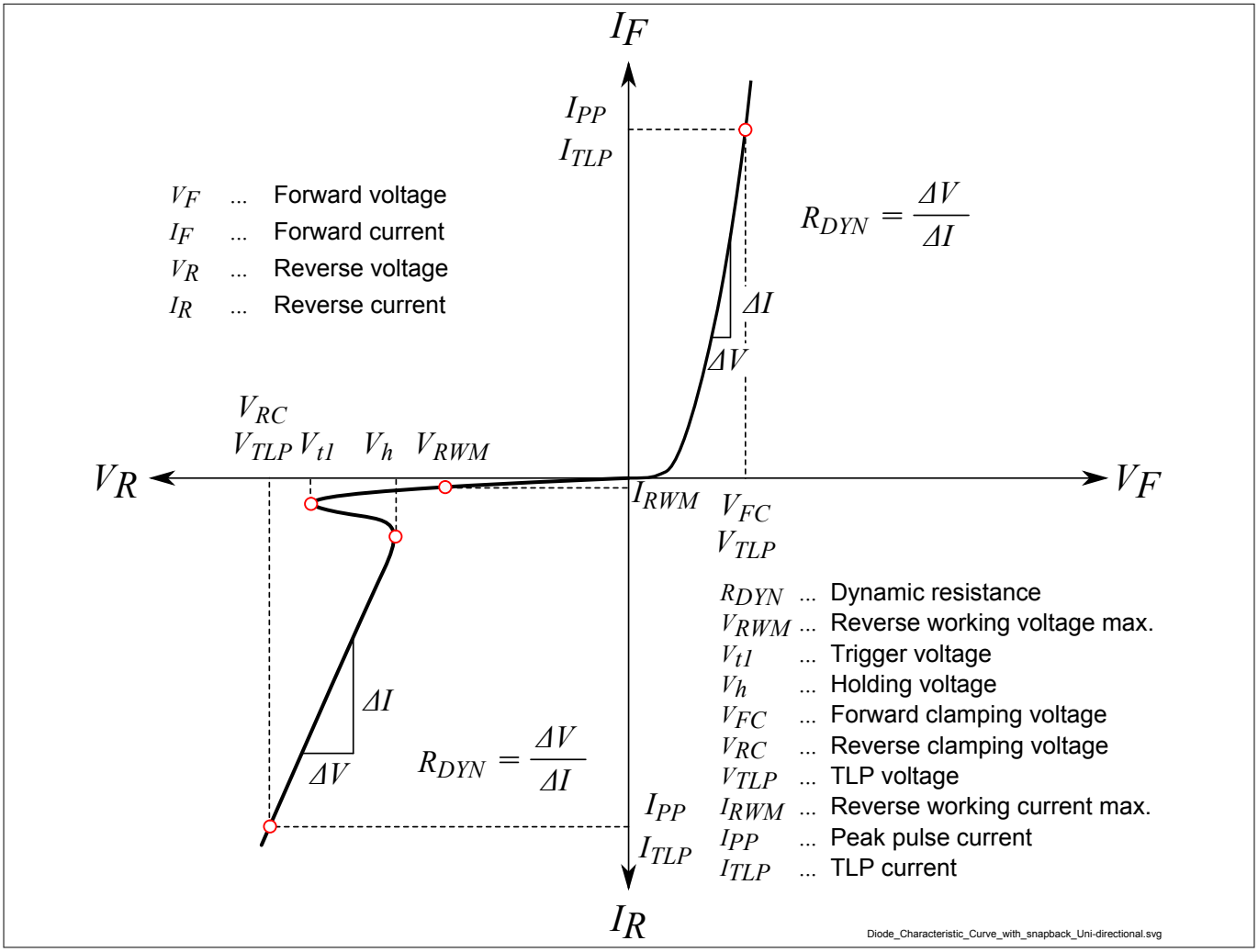

Figure 2 Definitions of electrical characteristics

Table 3 DC characteristics

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	–	–	5.5	V	I/O to GND
Reverse current	I_R	–	<1	100	nA	V_R = 5.5 V, I/O to GND

Table 4 RF characteristics

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	0.45	1	pF	V_R = 0 V, f = 1 MHz, I/O to GND
		–	0.23	0.5		V_R = 0 V, f = 1 MHz, I/O to I/O
Line capacitance	C_L	–	0.25	–	pF	V_R = 0 V, f = 825 MHz, I/O to GND
		–	0.13	–		V_R = 0 V, f = 825 MHz, I/O to I/O
Capacitance variation between I/O and GND	$\Delta C_{i/o\text{-}GND}$	–	0.02	–	pF	V_R = 0 V, f = 1 MHz, I/O to GND
Capacitance variation between I/O	$\Delta C_{i/o\text{-}i/o}$	–	0.01	–	pF	V_R = 0 V, f = 1 MHz, I/O to I/O

Table 5 ESD and surge characteristics

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Reverse clamping voltage [1]	V_{CL}	–	9	–	V	I_{PP} = 1 A, t_p = 8/20 µs, I/O pin to GND
		–	12	–		I_{PP} = 3 A, t_p = 8/20 µs, I/O pin to GND
Reverse clamping voltage [2]	V_{CL}	–	8.9	–	V	I_{TLP} = 16 A, t_p = 100 ns, I/O pin to GND
		–	11.5	–		I_{TLP} = 30 A, t_p = 100 ns, I/O pin to GND
Forward clamping voltage[1]	V_{FC}	–	1.75	–	V	I_{PP} = 1 A, t_p = 8/20 µs, GND pin to I/O
		–	2.5	–		I_{PP} = 3 A, t_p = 8/20 µs, GND pin to I/O
Forward clamping voltage [2]	V_{FC}	–	5.4	–	V	I_{TLP} = 16 A, t_p = 100 ns, GND pin to I/O
		–	9.2	–		I_{TLP} = 30 A, t_p = 100 ns, GND pin to I/O
Dynamic resistance[2]	R_{DYN}	–	0.2	–	Ω	I/O to GND
Dynamic resistance[2]	R_{DYN}	–	0.3	–	Ω	GND to I/O

1 I_{PP} according to IEC61000-4-5

2 Please refer to application note AN210 , TLP parameters: Z_0 = 50 Ω , t_p = 100 ns, t_r = 300 ps, averaging window: t_1 = 30 ns to t_2 = 60 ns, extraction of dynamic resistance using least squares fit of TLP characteristic between I_{PP1} = 10 A and I_{PP2} = 40 A.

3 Typical characteristic diagrams

Note: T_A = 25 °C, unless otherwise specified.

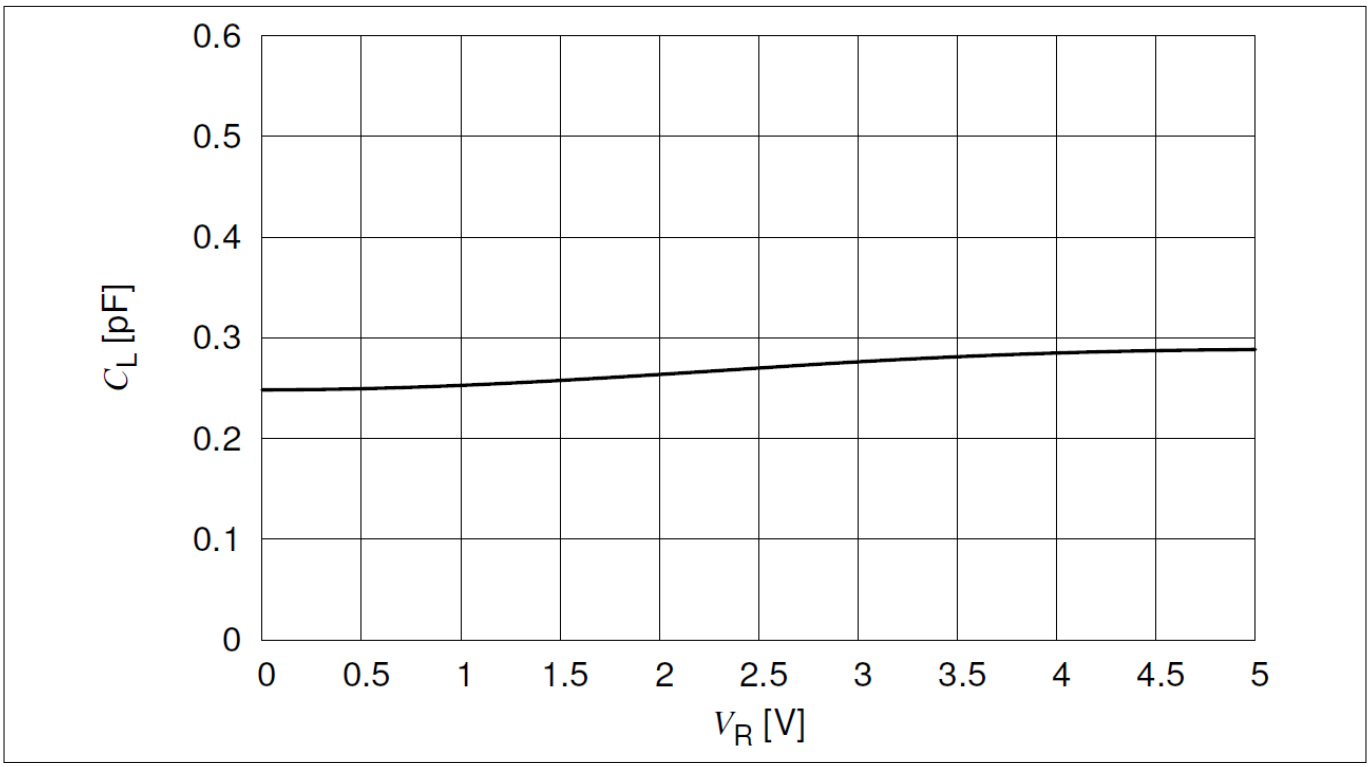

Figure 3 Line capacitance C_L = f(V_R) at f = 825 MHz

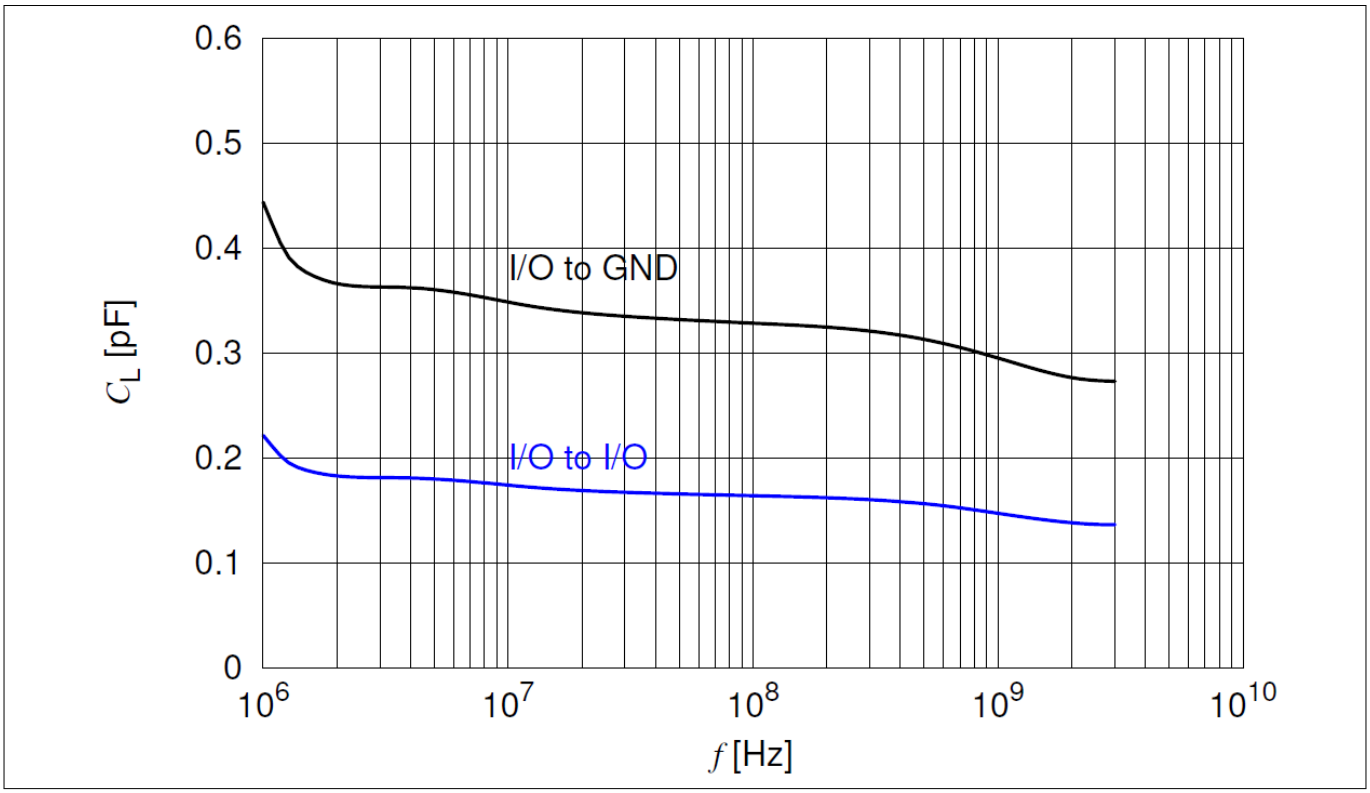

Figure 4 Line capacitance C_L = f(f), V_R = 0 V

Typical characteristic diagrams

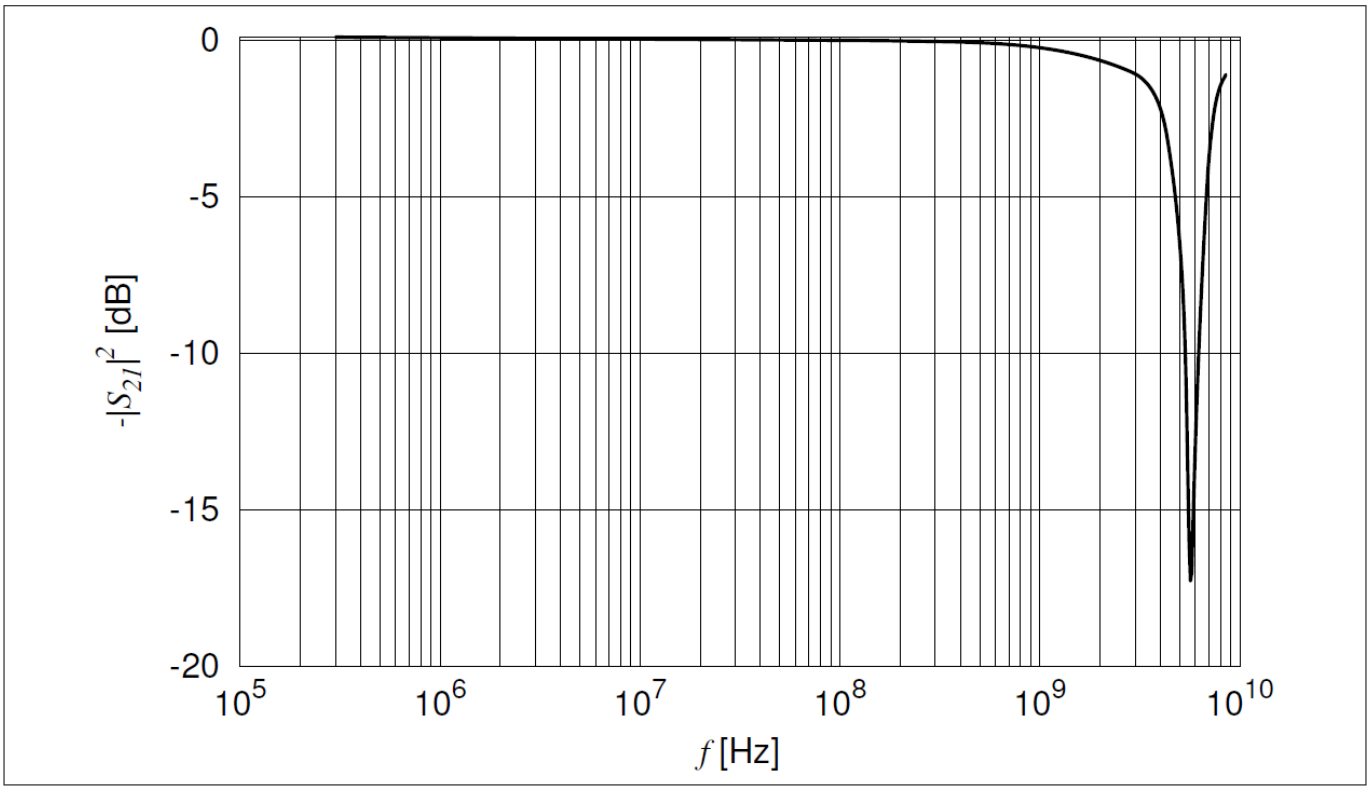

Figure 5 Insertion loss I_L= f(f), V_R = 0 V

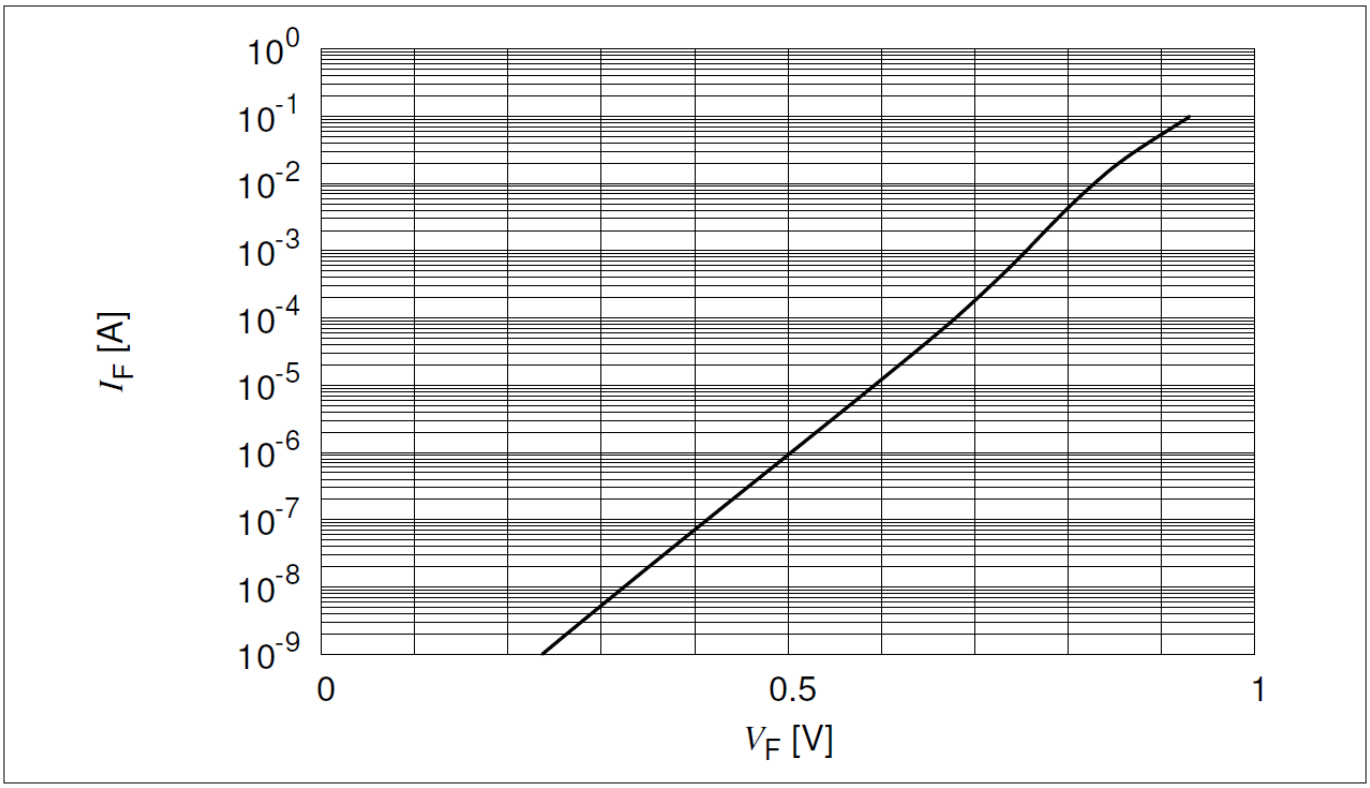

Figure 6 Forward characteristic, I_F = f(V_F), current forced

Typical characteristic diagrams

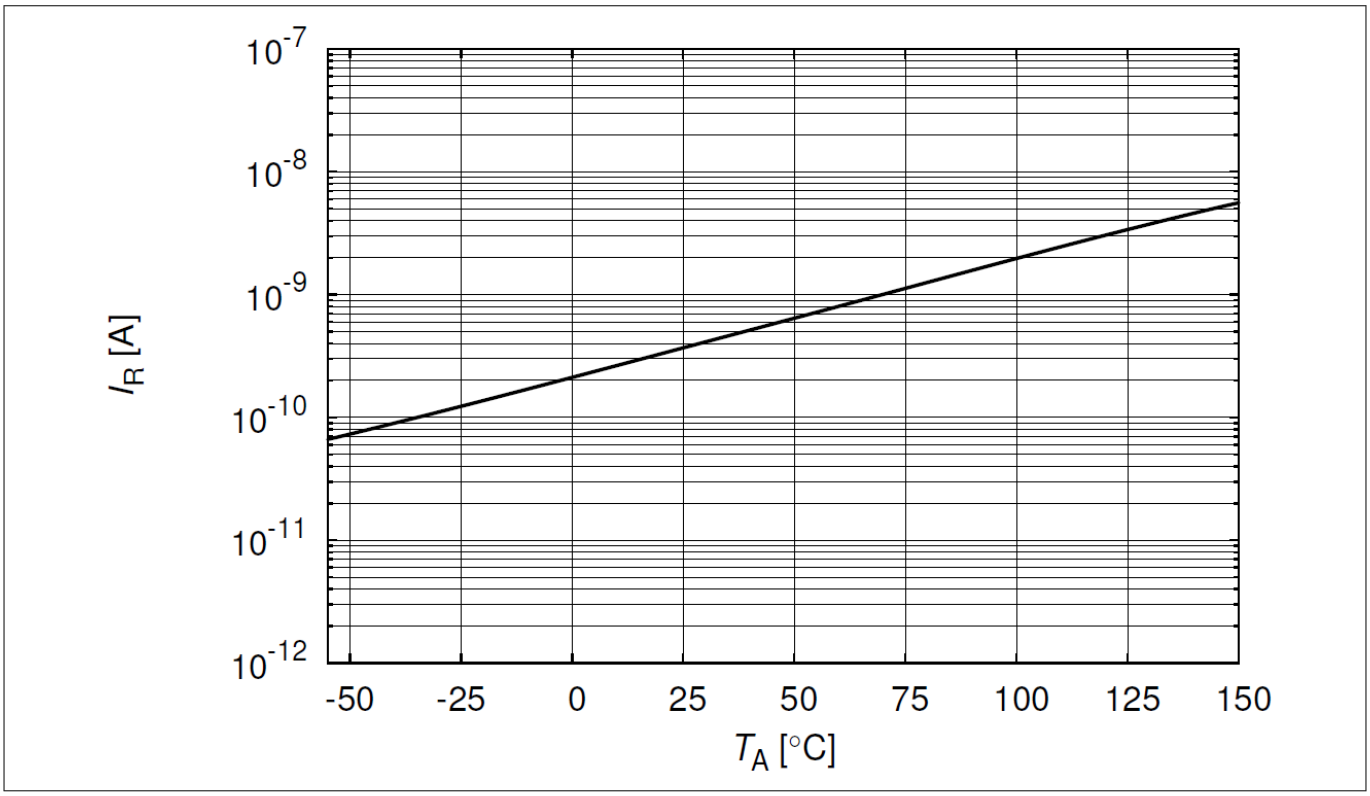

Figure 7 Reverse current I_R = f(T_A), V_R = 5.5 V (typical)

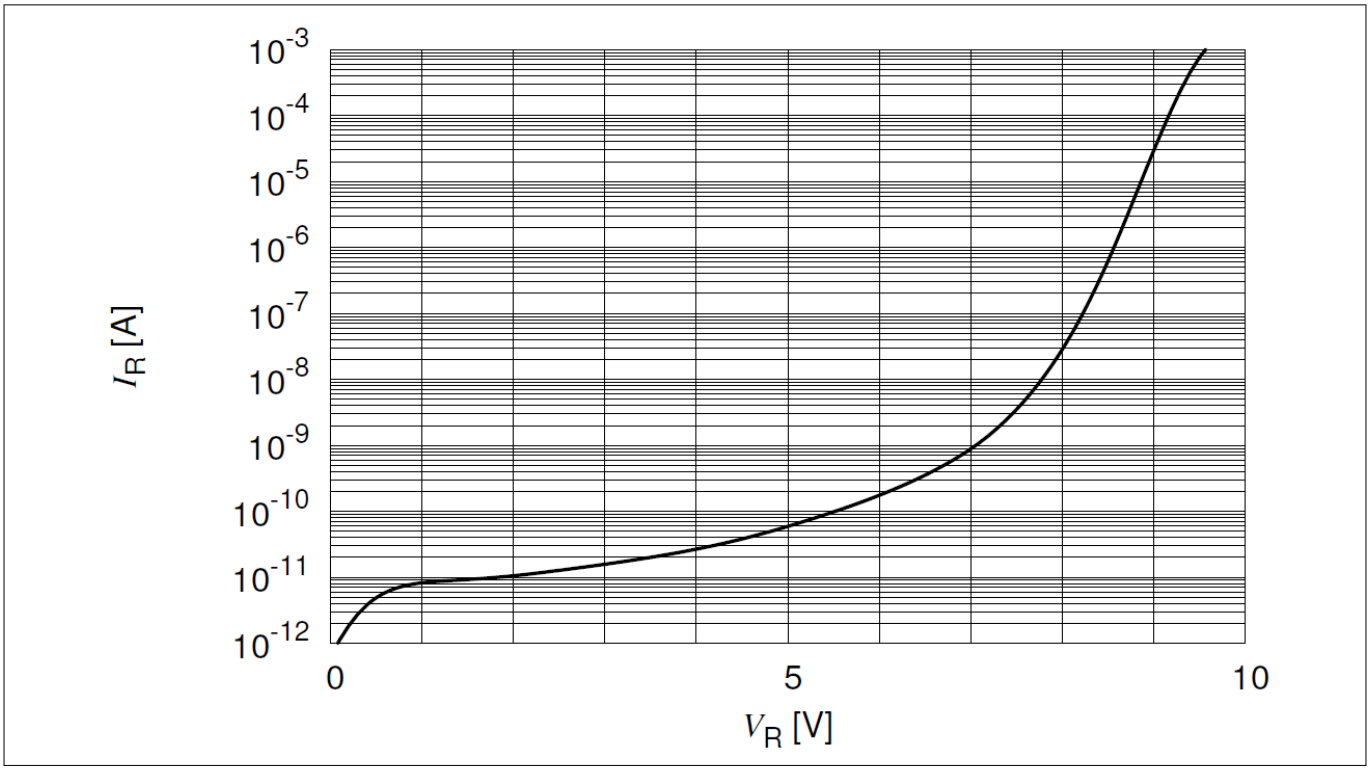

Figure 8 Reverse characteristic, I_R = (V_R), voltage forced

Typical characteristic diagrams

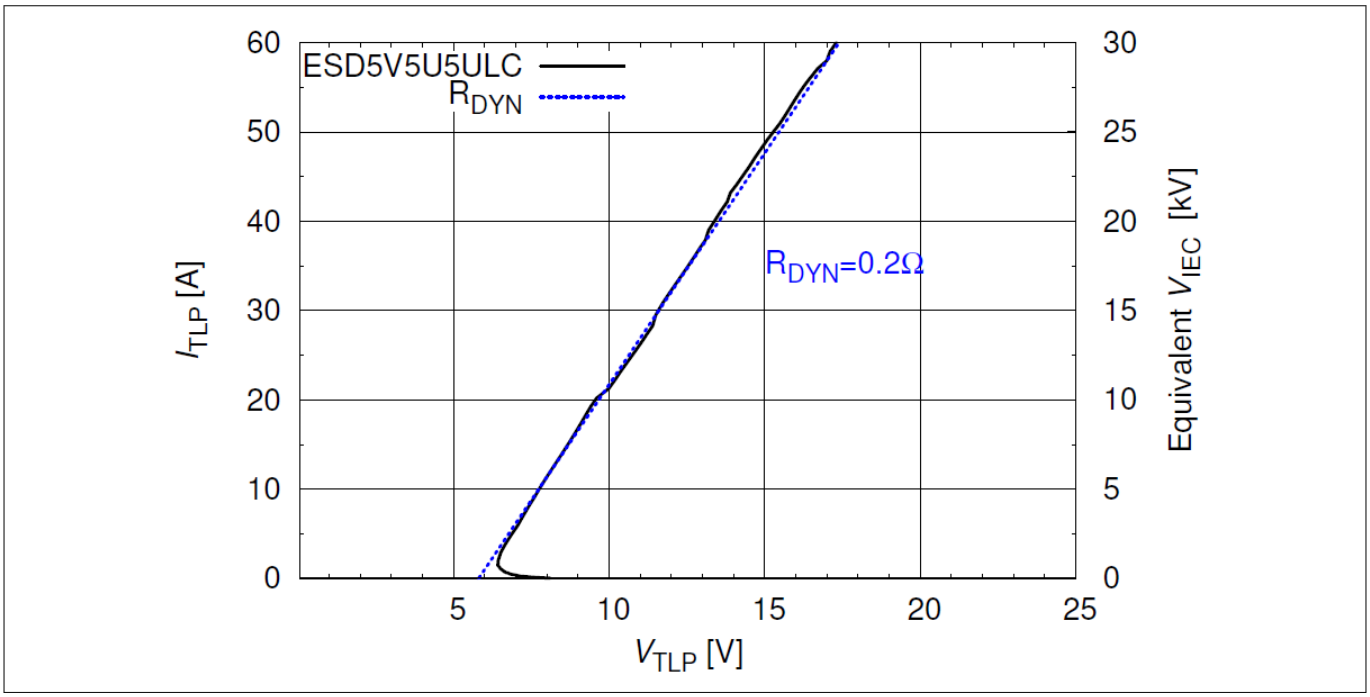

Figure 9 TLP characteristic I/O to GND [1)] *[1]*

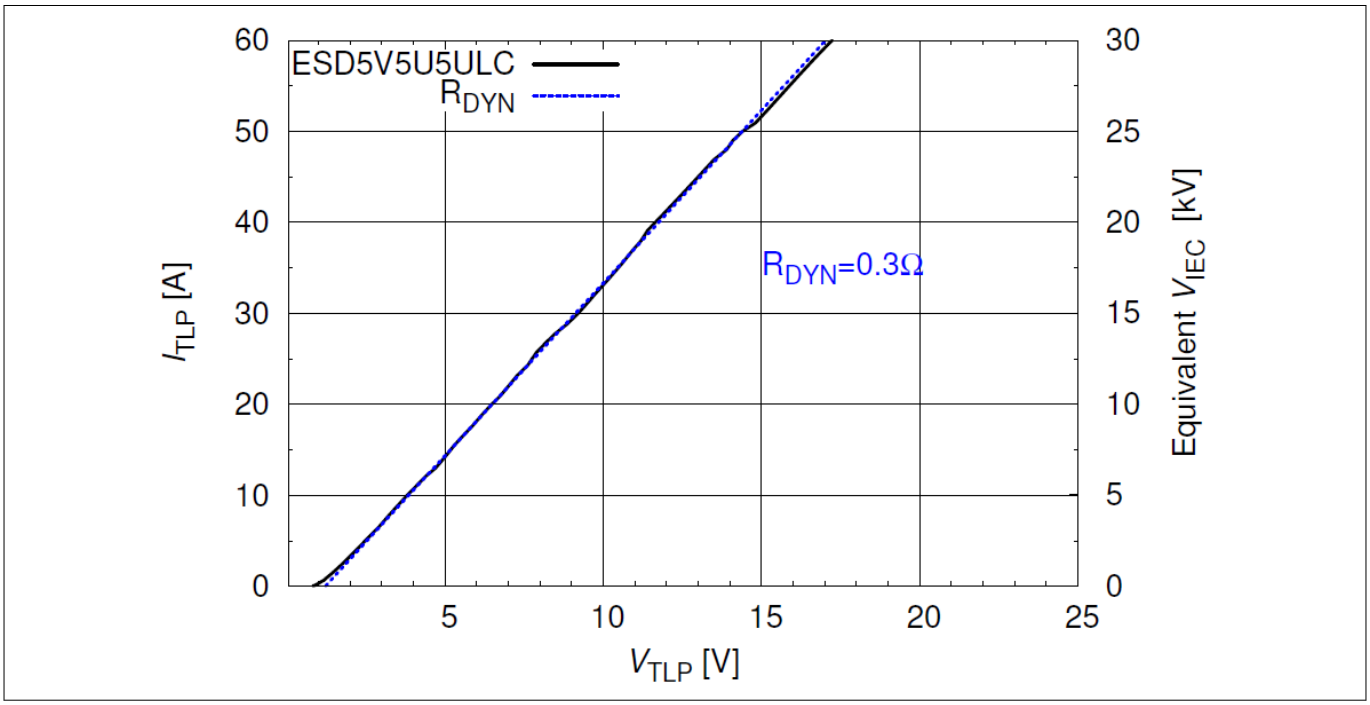

Figure 10 TLP characteristic GND to I/O [1)] *[1]*

1 TLP parameter: Z_0 = 50 Ω, t_p = 100 ns, t_r = 300 ps, averaging window: t_1 = 30 ns to t_2 = 60 ns, extraction of dynamic resistance using least squares fit of TLP characteristic between I_{PP1} = 10 A and I_{PP2} = 40 A. The equivalent stress level V_{IEC} according IEC61000-4-2 (R = 330 Ω , C = 150 pF) is calculated at the broad peak of the IEC waveform at t = 30 ns with 2 A/kV.

4 Application information

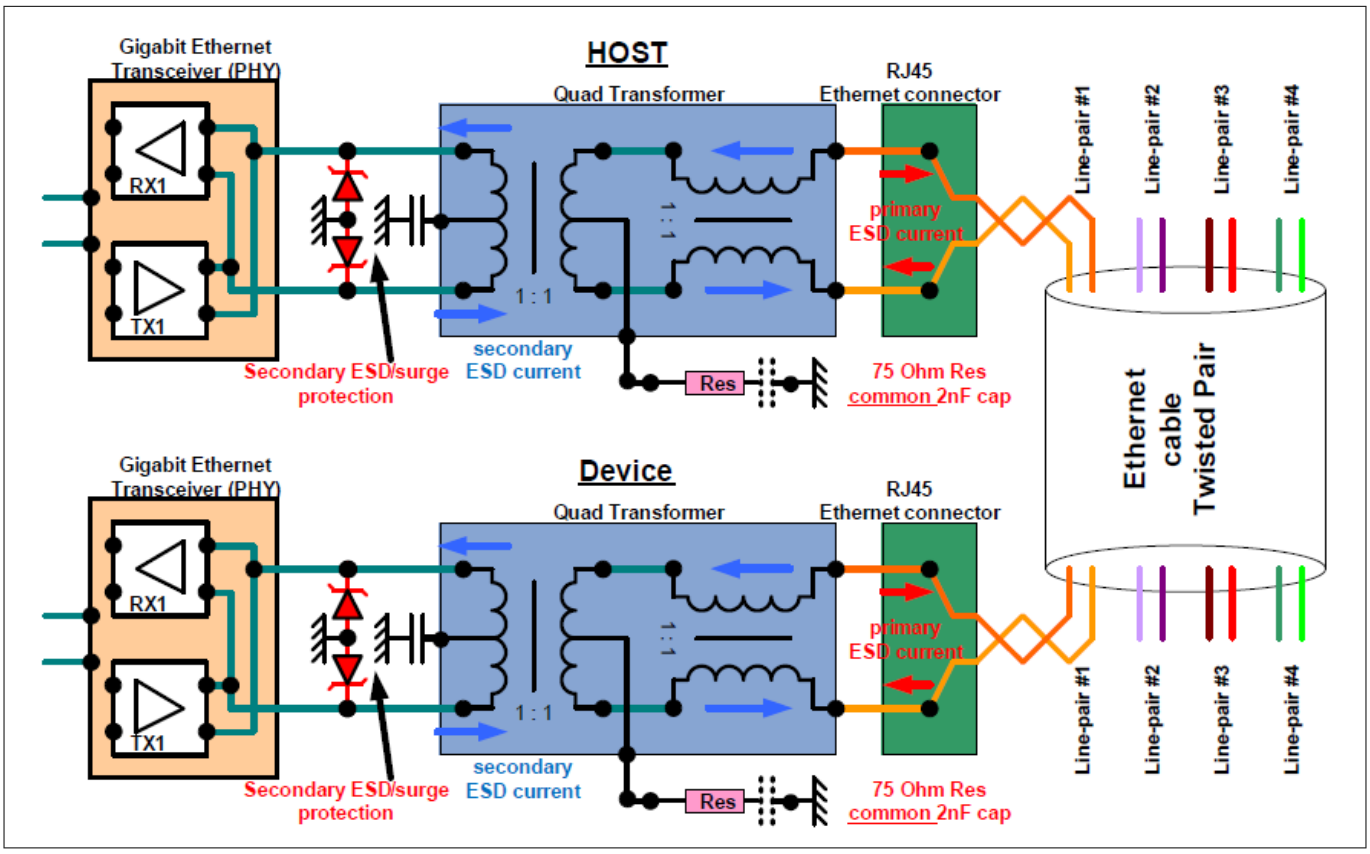

Figure 11 Ethernet

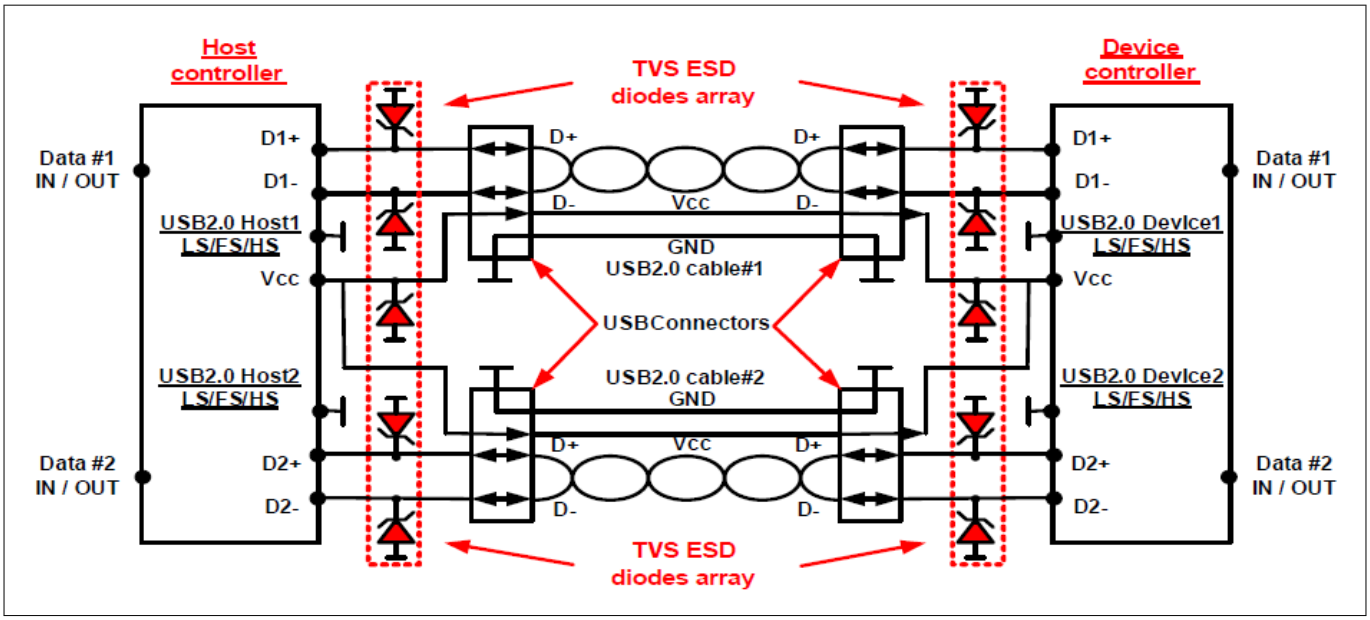

Figure 12 USB2.0

5 Package information

Note: Dimensions in mm.

5.1 PG-SC74-6-2 package

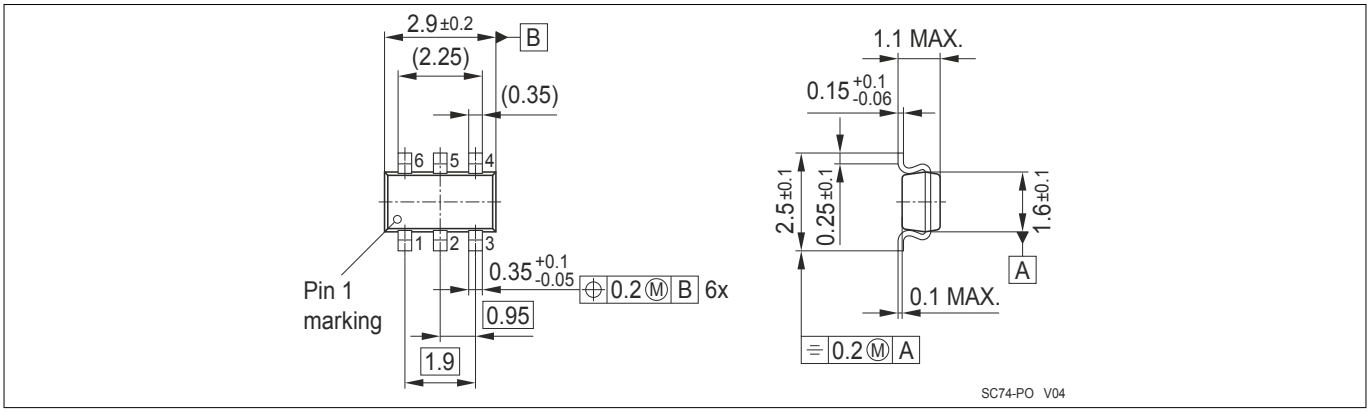

Figure 13 PG-SC74-6-2 package overview

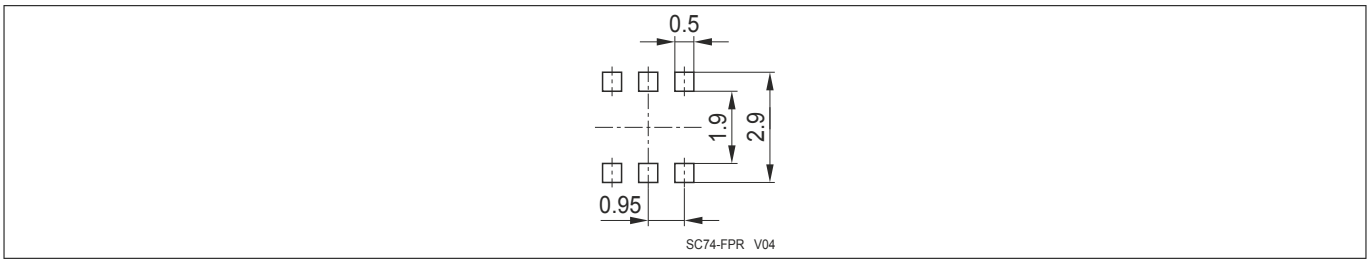

Figure 14 PG-SC74-6-2 footprint

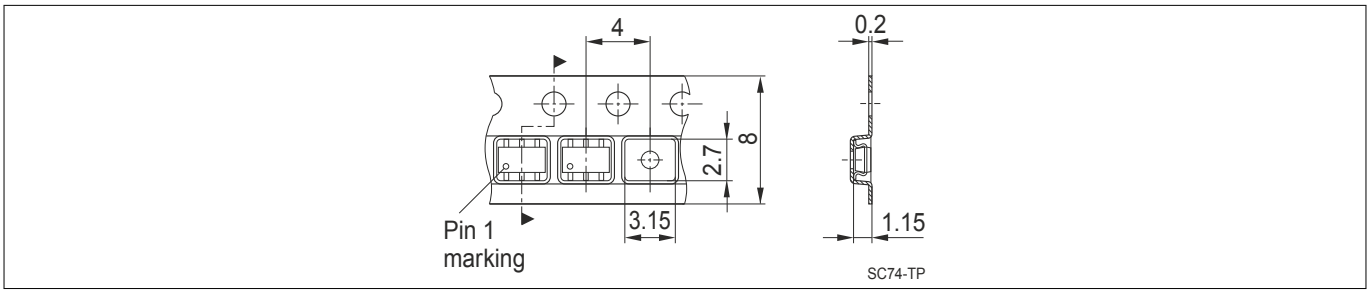

Figure 15 PG-SC74-6-2 packing

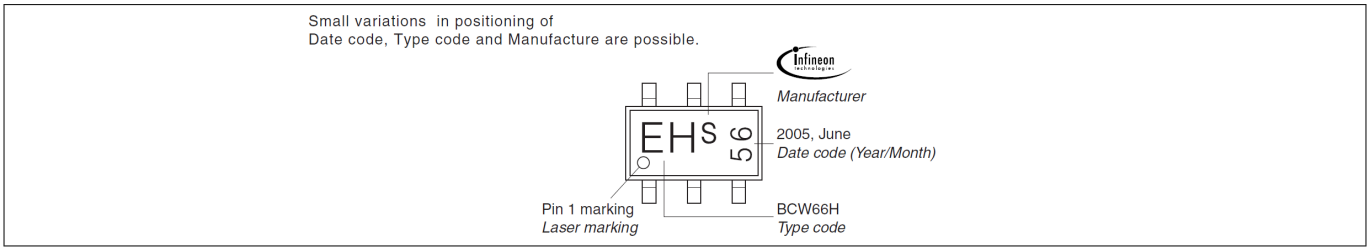

Figure 16 PG-SC74-6-2 marking example (see *Device information*)

6 References

[1] Infineon AG - **Application Note AN210**: Effective ESD protection design at system level using VF-TLP characterization methodology

Revision history

Revision history: Rev. 1.4. 2016-04-21	
Page or Item	**Subjects (major changes since previous revision)**
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All	Data sheet layout changed, references updated, ordering information scheme deleted

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